

# FDB44N25TM Datasheet



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DiGi Electronics Part Number FDB44N25TM-DG

Manufacturer onsemi

Manufacturer Product Number FDB44N25TM

Description MOSFET N-CH 250V 44A D2PAK

Detailed Description N-Channel 250 V 44A (Tc) 307W (Tc) Surface Mount

TO-263 (D2PAK)



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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
FDB44N25TM	onsemi
Series:	Product Status:
UniFET™	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
250 V	44A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	69mOhm @ 22A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
5V @ 250μA	61 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±30V	2870 pF @ 25 V
FET Feature:	Power Dissipation (Max):
	307W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
TO-263 (D2PAK)	TO-263-3, D2PAK (2 Leads + Tab), TO-263AB
Base Product Number:	
FDB44N25	

# **Environmental & Export classification**

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



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November 2013

## **FDB44N25**

# N-Channel UniFET<sup>TM</sup> MOSFET 250 V, 44 A, 69 m $\Omega$

### **Features**

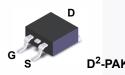
- $R_{DS(on)}$  = 69 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 22 A
- Low Gate Charge (Typ. 47 nC)
- Low C<sub>rss</sub> (Typ. 60 pF)
- · 100% Avalanche Tested

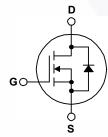
### **Applications**

- PDP TV
- · Lighting
- · Uninterruptible Power Supply
- · AC-DC Power Supply

# **Description**

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter			FDB44N25	Unit	
V <sub>DSS</sub>	Drain-Source Voltage			250	V	
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)		44 26.4	A A	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	176	Α	
V <sub>GSS</sub>	Gate-Source voltage	Gate-Source voltage				
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		(Note 2)	2055	mJ	
I <sub>AR</sub>	Avalanche Current (Not		(Note 1)	44	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		(Note 1)	30.7	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		(Note 3)	4.5	V/ns	
$P_{D}$	Power Dissipation	(T <sub>C</sub> = 25°C) - Derate Above 25°C			W/°C	
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

### **Thermal Characteristics**

Symbol	Parameter	FDB44N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.41	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (1 in <sup>2</sup> Pad of 2-oz Copepr), Max. 40		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambien (Minimum Pad of 2-oz Copper), Max. 62.5		

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDB44N25TM	FDB44N25	D <sup>2</sup> -PAK	Tape and Reel	330 mm	24 mm	800 units

# $\textbf{Electrical Characteristics} \quad \textbf{T}_{C} = 25^{\circ} \text{C unless otherwise noted}.$

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	Off Characteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V, } I_D = 250  \mu\text{A}$	250			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.25		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 200 V, T <sub>C</sub> = 125°C			1 10	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V	-		100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Charac	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 22 A		0.058	0.069	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 22 A		32		S
Dynamic C	haracteristics				•	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,		2210	2870	pF
C <sub>oss</sub>	Output Capacitance	f = 1 MHz		450	585	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			60	90	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 125 V, I <sub>D</sub> = 44 A,		55	120	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS}$ = 10 V, $R_G$ = 25 $\Omega$	-	400	810	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	85	180	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		115	240	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 200 V, I <sub>D</sub> = 44 A,	/	47	61	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		18		nC
$Q_{gd}$	Gate-Drain Charge	(Note 4)		24		nC
Drain-Sour	rce Diode Characteristics and Maximun	n Ratings				
I <sub>S</sub>	S Maximum Continuous Drain-Source Diode Forward Current				44	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		-		176	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 44 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 44 A,		195		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> /dt =100 A/μs		1.8		μС

### Notes:

<sup>1.</sup> Repetitive rating: pulse-width limited by maximum junction temperature.

<sup>2.</sup> L = 1.7 mH,  $I_{AS}$  = 44 A,  $V_{DD}$  = 50 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C.

<sup>3.</sup>  $I_{SD} \le 44$  A, di/dt  $\le 200$  A/ $\mu$ s,  $V_{DD} \le BV_{DSS}$ , starting  $T_J$  = 25°C.

<sup>4.</sup> Essentially independent of operating temperature typical characteristics.

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

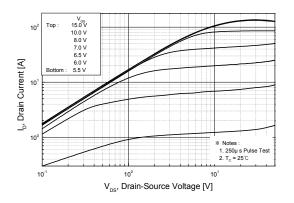


Figure 2. Transfer Characteristics

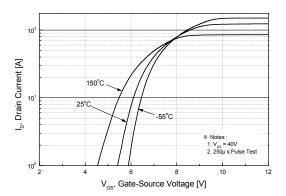
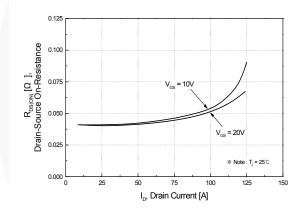


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue



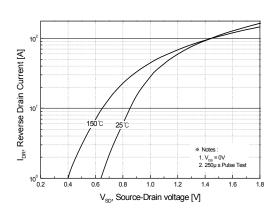


Figure 5. Capacitance Characteristics

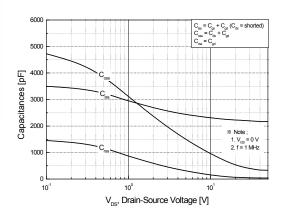
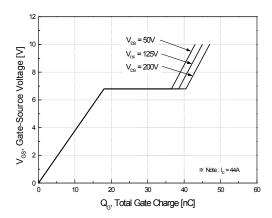


Figure 6. Gate Charge Characteristics



# **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

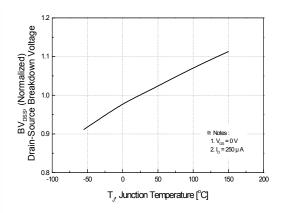


Figure 8. On-Resistance Variation vs. Temperature

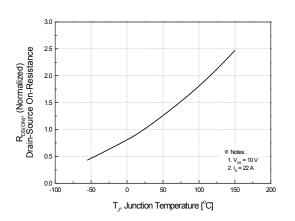
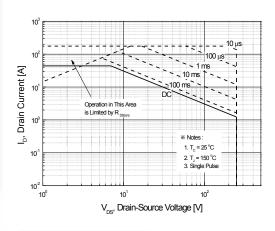


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature



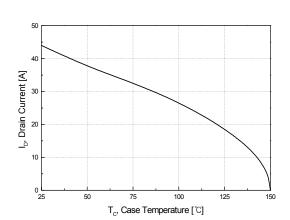
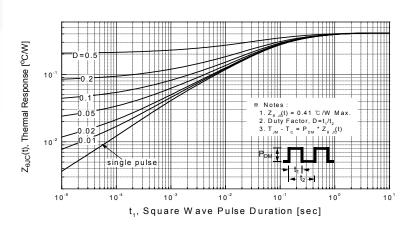


Figure 11. Transient Thermal Response Curve



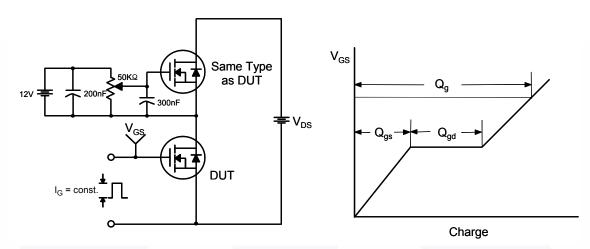


Figure 12. Gate Charge Test Circuit & Waveform

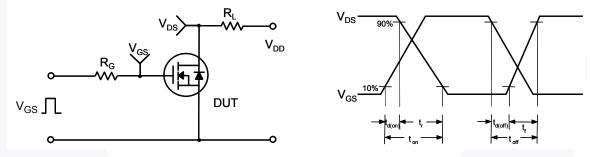


Figure 13. Resistive Switching Test Circuit & Waveforms

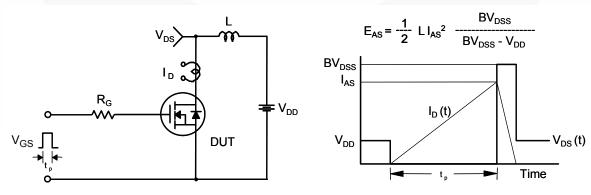


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

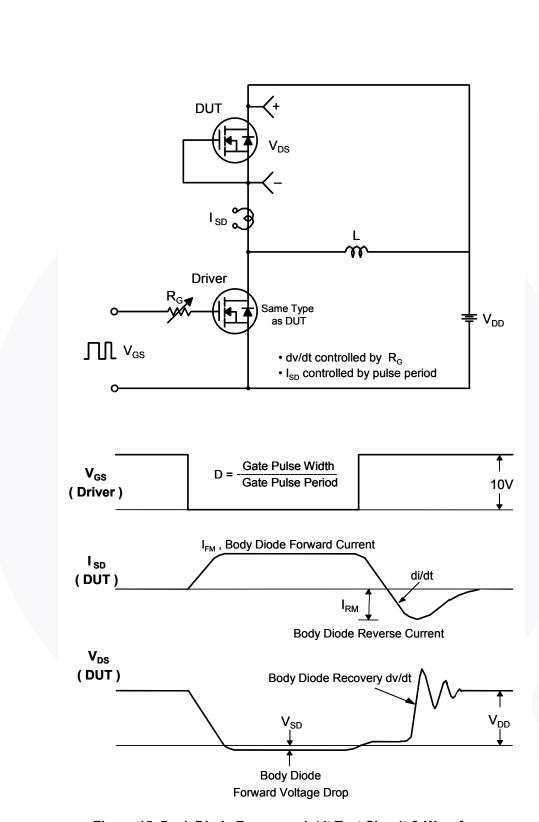


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

### **Mechanical Dimensions**

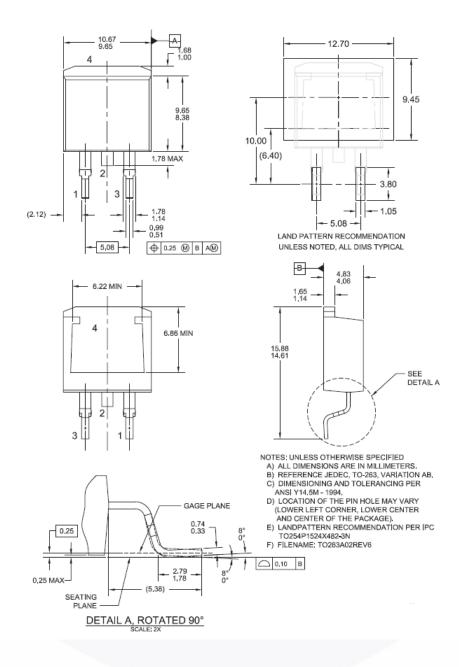


Figure 16. TO263 (D<sup>2</sup>PAK), Molded, 2-Lead, Surface Mount

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